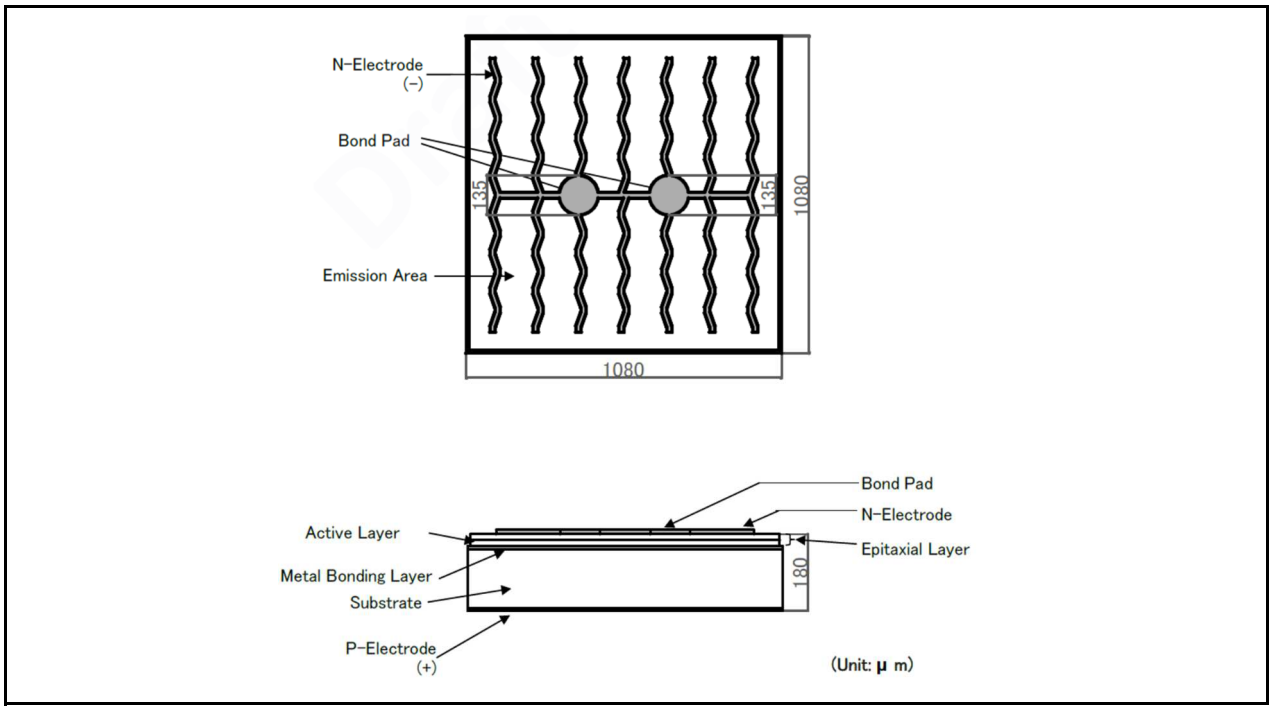
EPIGAP Optronic GmbH
Koepenicker Str. 325
D-12555 Berlin
Fon: +49 (0)30 657637 60
Fax: +49 (0)30 657637 70
sales@epigap-optronic.de

Data Sheet — Preliminary

Infrared LED Chip — EOLC-1550-21

Rev. 02, 2020

Radiation	Type	Electrodes
Infrared	InGaAs - based material	n (cathode) up



Die size (typ.): 1.080 mm × 1.080 mm (42 mil)
Thickness (typ.): 0.180 mm (7 mil)
Bond pads size: Ø 0.130 mm (perifery = Ø 0.135 mm)
Contact metallization anode and cathode: gold alloy

Maximum Ratings

T_{amb}= 25°C, unless otherwise specified

Parameter	Test Conditions	Symbol	Value	Unit
Continuous forward current*		I_F	1000	mA
Peak forward current*		I_{FP}	2000	mA
Reverse current	I_R= 5 V	I_R	10	µA
Junction temperature		T_J	120	°C

*For reference only

RoHS COMPLIANT Pb-Free

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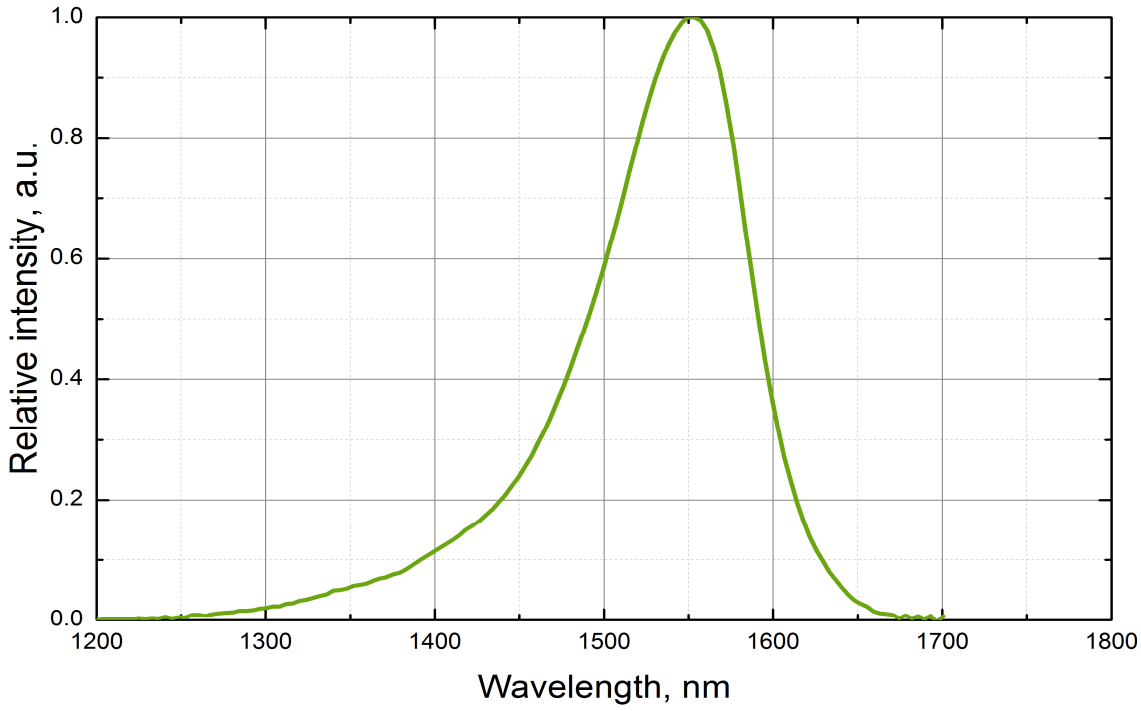
Optical and Electrical Characteristics

T_{amb}= 25°C, unless otherwise specified

Parameter	Test cond.	Symbol	Min	Typ	Max	Unit
Forward voltage	I_F=20 mA	V_F		0.74		V
Radiant power*	I_F=20 mA	Φ_e		3.3		mW
Peak wavelength	I_F=20 mA	λ_p	1500	1550	1600	nm
FWHM	I_F=20 mA	$\Delta\lambda_{0.5}$		90		nm
Forward voltage	I_F=350 mA	V_F		1	1.3	V
Radiant power*	I_F=350 mA	Φ_e		30		mW
Peak wavelength	I_F=350 mA	λ_p	1500	1550		nm
FWHM	I_F=350 mA	$\Delta\lambda_{0.5}$		120		nm
Forward voltage	I_F=1000 mA	V_F		1	1.4	V
Radiant power*	I_F=1000 mA	Φ_e		50		mW
Peak wavelength	I_F=1000 mA	λ_p	1500	1550		nm
FWHM	I_F=1000 mA	$\Delta\lambda_{0.5}$		120		nm

*Measured on silicon covered chip on star board



Spectrum at 350 mA

Art. No. 131 176